

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5411

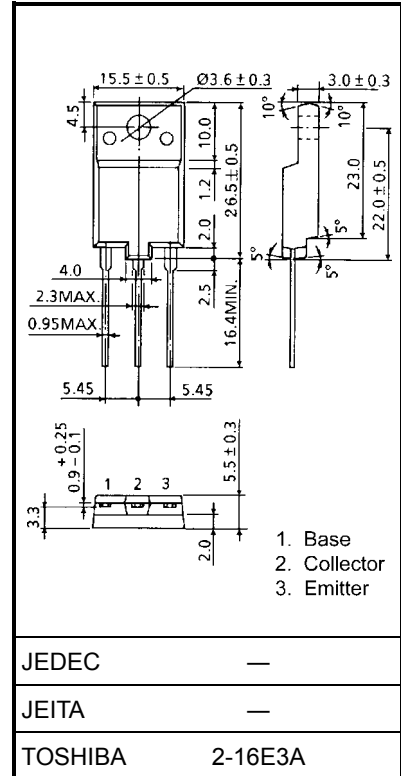
HORIZONTAL DEFLECTION OUTPUT FOR HIGH RESOLUTION

DISPLAY, COLOR TV

HIGH SPEED SWITCHING APPLICATIONS

- High Voltage : $V_{CBO} = 1500\text{ V}$
- Low Saturation Voltage : $V_{CE(sat)} = 3\text{ V (Max.)}$
- High Speed : $t_f = 0.15\text{ }\mu\text{s (Typ.)}$
- Collector Metal (Fin) is Fully Covered with Mold Resin.

Unit: mm



Weight: 5.5 g (typ.)

MAXIMUM RATINGS (Tc = 25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1500	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	14	A
	Pulse	I_{CP}	28	
Base Current		I_B	7	A
Collector Power Dissipation		P_C	60	W
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55~150	°C

ELECTRICAL CHARACTERISTICS (Tc = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN	TYP.	MAX	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	—	—	10	μA
Emitter-Base Breakdown Voltage		$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	600	—	—	V
DC Current Gain	$h_{FE(1)}$	$V_{CE} = 5\text{ V}, I_C = 2\text{ A}$	10	—	40		
	$h_{FE(2)}$	$V_{CE} = 5\text{ V}, I_C = 11\text{ A}$	4	—	8		
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 11\text{ A}, I_B = 2.75\text{ A}$	—	—	3	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 11\text{ A}, I_B = 2.75\text{ A}$	—	1.0	1.5	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	190	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 8.5\text{ A}, I_{B1}(\text{end}) = 1.6\text{ A}$ $f_H = 64\text{ kHz}$	—	2.5	3.5	μs
	Fall Time	t_f		—	0.15	0.3	

